# BZX84 series Voltage regulator diodes Rev. 6 — 6 March 2014

Product data sheet

## 1. Product profile

## 1.1 General description

Low-power voltage regulator diodes in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

The diodes are available in the normalized E24  $\pm 1$  % (BZX84-A),  $\pm 2$  % (BZX84-B) and approximately  $\pm 5$  % (BZX84-C) tolerance range. The series includes 37 breakdown voltages with nominal working voltages from 2.4 V to 75 V.

#### 1.2 Features and benefits

- Total power dissipation: ≤ 250 mW
- Three tolerance series: ±1 %, ±2 % and approximately ±5 %
- AEC-Q101 qualified

- Working voltage range: nominal 2.4 V to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: ≤ 40 W

## 1.3 Applications

General regulation functions

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	I <sub>F</sub> = 10 mA [1]	-	-	0.9	V
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$ [2]	-	-	250	mW

<sup>[1]</sup> Pulse test:  $t_p \leq 100~\mu s;~\delta \leq 0.02$ 



<sup>[2]</sup> Device mounted on a FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 2. Pinning information

Table 2. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		
2	n.c.	not connected		
3	K	cathode		A n.c.
			1 2	aaa-006592

# 3. Ordering information

Table 3. Ordering information

Type number	Package									
	Name	Description	Version							
BZX84 series[1]	TO-236AB	plastic surface-mounted package; 3 leads	SOT23							

<sup>[1]</sup> The series includes 37 breakdown voltages with nominal working voltages from 2.4 V to 75 V and  $\pm 1$  %,  $\pm 2$  % and  $\pm 5$  % tolerances.

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>	Type number	Marking code[1]
BZX84-A2V4	*50	BZX84-A18	KF*
BZX84-A2V7	*51	BZX84-A20	*C2
BZX84-A3V0	*52	BZX84-A22	KG*
BZX84-A3V3	*53	BZX84-A24	KH*
BZX84-A3V6	*C1	BZX84-A27	*75
BZX84-A3V9	*55	BZX84-A30	KJ*
BZX84-A4V3	*56	BZX84-A33	KK*
BZX84-A4V7	*57	BZX84-A36	*C3
BZX84-A5V1	*58	BZX84-A39	*C4
BZX84-A5V6	*59	BZX84-A43	*C5
BZX84-A6V2	*60	BZX84-A51	*C6
BZX84-A6V8	*61	BZX84-A75	*86
BZX84-A7V5	*62	BZX84-B2V4	*Z0
BZX84-A8V2	*63	BZX84-B2V7	*Z1
BZX84-A9V1	*64	BZX84-B3V0	*S1
BZX84-A10	*65	BZX84-B3V3	*S2
BZX84-A11	*04	BZX84-B3V6	*S3
BZX84-A12	*67	BZX84-B3V9	*S4
BZX84-A13	*C0	BZX84-B4V3	*S7
BZX84-A15	*69	BZX84-B4V7	*S8
BZX84-A16	KE*	BZX84-B5V1	*R1

 Table 4.
 Marking codes ...continued

Type number	Marking code <sup>[1]</sup>	Type number	Marking code <sup>[1]</sup>		
BZX84-B5V6	*R2	BZX84-C3V9	*B3		
BZX84-B6V2	*R5	BZX84-C4V3	*B6		
BZX84-B6V8	*R6	BZX84-C4V7	Z1*		
BZX84-B7V5	*R8	BZX84-C5V1	Z2*		
BZX84-B8V2	*R9	BZX84-C5V6	Z3*		
BZX84-B9V1	*T1	BZX84-C6V2	Z4*		
BZX84-B10	*66	BZX84-C6V8	Z5*		
BZX84-B11	*Z6	BZX84-C7V5	Z6*		
BZX84-B12	*Z7	BZX84-C8V2	Z7*		
BZX84-B13	*Z8	BZX84-C9V1	Z8*		
BZX84-B15	*Z9	BZX84-C10	Z9*		
BZX84-B16	*70	BZX84-C11	Y1*		
BZX84-B18	*71	BZX84-C12	Y2*		
BZX84-B20	*72	BZX84-C13	Y3*		
BZX84-B22	*73	BZX84-C15	Y4*		
BZX84-B24	*74	BZX84-C16	Y5*		
BZX84-B27	*Z5	BZX84-C18	Y6*		
BZX84-B30	*Z4	BZX84-C20	Y7*		
BZX84-B33	*Y1	BZX84-C22	Y8*		
BZX84-B36	*Y2	BZX84-C24	Y9*		
BZX84-B39	*S0	BZX84-C27	*T2		
BZX84-B43	*S5	BZX84-C30	*T5		
BZX84-B47	*S6	BZX84-C33	*T6		
BZX84-B51	*S9	BZX84-C36	*T7		
BZX84-B56	*R0	BZX84-C39	*T8		
BZX84-B62	*R3	BZX84-C43	*B4		
BZX84-B68	*R4	BZX84-C47	*B5		
BZX84-B75	*R7	BZX84-C51	*B7		
BZX84-C2V4	*T3	BZX84-C56	*B8		
BZX84-C2V7	*T4	BZX84-C62	*B9		
BZX84-C3V0	*T9	BZX84-C68	*B0		
BZX84-C3V3	*B1	BZX84-C75	*A1		
BZX84-C3V6	*B2	-	-		

<sup>[1] \* =</sup> placeholder for manufacturing site code

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$I_{F}$	forward current		-	200	mA
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation	[1]	-	40	W
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$ [2]	-	250	mW
T <sub>amb</sub>	ambient temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-55	+150	°C
Tj	junction temperature		-65	+150	°C

<sup>[1]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \,^{\circ}C$  before surge

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[2]	-	-	330	K/W

<sup>[1]</sup> Device mounted on a FR4 PCB, single-sided copper, tin-plated and standard footprint.

## 7. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	I <sub>F</sub> = 10 mA [1]	-	-	0.9	V

<sup>[1]</sup> Pulse test:  $t_p \le 100~\mu s;~\delta \le 0.02$ 

<sup>[2]</sup> Device mounted on a FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Soldering point of cathode tab.

Table 8. Characteristics per type; BZX84-A2V4 to BZX84-C24

BZX84- xxx			je		rential	resista	ance	Reve curre I <sub>R</sub> (μΑ	ent		erature icient V/K)		Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current
		I <sub>Z</sub> = 5	mA	I <sub>Z</sub> = 1	mA	I <sub>Z</sub> = 5	mA			I <sub>Z</sub> = 5	mA			I <sub>ZSM</sub> (A)[2]
		Min	Max	Тур	Max	Тур	Max	Max	V <sub>R</sub> (V)	Min	Тур	Max	Max	Max
2V4	Α	2.37	2.43	275	600	70	100	50	1	-3.5	-1.6	0	450	6.0
	В	2.35	2.45											
	С	2.2	2.6											
2V7	Α	2.67	2.73	300	600	75	100	20	1	-3.5	-2.0	0	450	6.0
	В	2.65	2.75											
	С	2.5	2.9											
3V0	Α	2.97	3.03	325	600	80	95	10	1	-3.5	-2.1	0	450	6.0
	В	2.94	3.06											
	С	2.8	3.2											
3V3	Α	3.26	3.34	350	600	85	95	5	1	-3.5	-2.4	0	450	6.0
	В	3.23	3.37											
	С	3.1	3.5											
3V6	Α	3.56	3.64	375	600	85	90	5	1	-3.5	-2.4	0	450	6.0
	В	3.53	3.67											
	С	3.4	3.8											
3V9	Α	3.86	3.94	400	600	85	90	3	1	-3.5	-2.5	0	450	6.0
	В	3.82	3.98											
	С	3.7	4.1											
4V3	Α	4.25	4.35	410	600	80	90	3	1	-3.5	-2.5	0	450	6.0
	В	4.21	4.39											
	С	4.0	4.6											
4V7	Α	4.65	4.75	425	500	50	80	3	2	-3.5	-1.4	0.2	300	6.0
	В	4.61	4.79											
	С	4.4	5.0											
5V1	Α	5.04	5.16	400	480	40	60	2	2	-2.7	-0.8	1.2	300	6.0
	В	5.0	5.2											
	С	4.8	5.4											
5V6	Α	5.54	5.66	80	400	15	40	1	2	-2.0	1.2	2.5	300	6.0
	В	5.49	5.71											
	С	5.2	6.0											
6V2	Α	6.13	6.27	40	150	6	10	3	4	0.4	2.3	3.7	200	6.0
	В	6.08	6.32											
	С	5.8 6.6												
6V8	Α	6.73	6.87	30	80	6	15	2	4	1.2	3.0 4.5	200	6.0	
	В	6.66	6.94		00	б	13		4	1.2 3.0	3.0	.0 200	0.0	
_	С	6.4	7.2											

Table 8. Characteristics per type; BZX84-A2V4 to BZX84-C24 ...continued

BZX84- xxx	Sel	Worki voltag V <sub>Z</sub> (V)	e	Differ	rential 2)	resist	ance	Reve curre I <sub>R</sub> (μΑ	ent		erature icient nV/K)	)	Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current
		I <sub>Z</sub> = 5	mA	I <sub>Z</sub> = 1	mA	$I_Z = 5$	mA			$I_Z = 5$	mA			I <sub>ZSM</sub> (A)[2]
		Min	Max	Тур	Max	Тур	Max	Max	V <sub>R</sub> (V)	Min	Тур	Max	Max	Max
7V5	Α	7.42	7.58	30	80	6	15	1	5	2.5	4.0	5.3	150	4.0
	В	7.35	7.65											
	С	7.0	7.9											
8V2	Α	8.11	8.29	40	80	6	15	0.7	5	3.2	4.6	6.2	150	4.0
	В	8.04	8.36											
	С	7.7	8.7											
9V1	Α	9	9.2	40	100	6	15	0.5	6	3.8	5.5	7.0	150	3.0
	В	8.92	9.28											
	С	8.5	9.6											
10	Α	9.9	10.1	50	150	8	20	0.2	7	4.5	6.4	8.0	90	3.0
	В	9.8 10.2												
	С	9.4	10.6											
11	Α	10.8	11.11	50	150	10	20	0.1	8	5.4	7.4	9.0	85	2.5
	В	10.8	11.2											
	С	10.4	11.6											
12	Α	11.88	12.12	12 50 1	150	10	25	0.1	8	6.0	8.4	10.0	85	2.5
	В	11.8	12.2											
	С	11.4	12.7											
13	Α	12.87	13.13	50	170	10	30	0.1	8	7.0	9.4	11.0	80	2.5
	В	12.7	13.3											
	С	12.4	14.1											
15	Α	14.85	15.15	50	200	10	30	0.05	10.5	9.2	11.4	13.0	75	2.0
	В	14.7	15.3											
	С	13.8	15.6											
16	Α	15.84	16.16	50	200	10	40	0.05	11.2	10.4	12.4	14.0	75	1.5
	В	15.7	16.3											
	С	15.3	17.1											
18	Α	17.82	18.18	50	225	10	45	0.05	12.6	12.4	14.4	16.0	70	1.5
	В	17.6	18.4											
	С	16.8	19.1											
20	Α	19.8	20.2	60	225	15	55	0.05	14	14.4	16.4	18.0	60	1.5
	В	19.6	20.4											
	С	18.8	21.2											
22	Α	21.78	22.22	60	250	20	55	0.05	15.4	16.4	18.4	20.0	60	1.25
	В	21.6	22.4	1		20	55 0.05		7 13.4	4 10.4 16.	10.4	20.0		
	С	20.8	23.3	Ť										

Table 8. Characteristics per type; BZX84-A2V4 to BZX84-C24 ...continued

 $T_i = 25$  °C unless otherwise specified.

BZX84- xxx	voltage V <sub>Z</sub> (V)		voltage V <sub>Z</sub> (V)		ential 2)	resista	ince			Tempo coeffic S <sub>Z</sub> (m <sup>3</sup>			Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current
		$I_Z = 5$ ı	nΑ	I <sub>Z</sub> = 1	mA	I <sub>Z</sub> = 5	mA	I		$I_Z = 5 \text{ mA}$			I <sub>ZSM</sub> (A)[2]	
		Min	Max	Тур	Max	Тур	Max	Max	V <sub>R</sub> (V)	Min	Тур	Max	Max	Max
24	Α	23.76	24.24	60	250	25	70	0.05	16.8	18.4	20.4	22.0	55	1.25
	В	23.5	24.5											
	С	22.8	25.6	Ī										

<sup>[1]</sup>  $f = 1 \text{ MHz}; V_R = 0 \text{ V}$ 

Table 9. Characteristics per type; BZX84-A27 to BZX84-C75

 $T_j = 25$  °C unless otherwise specified.

BZX84- xxx	Sel	Worki voltag V <sub>Z</sub> (V)	•	Differ	rential 2)	resista	ance	Reve curre I <sub>R</sub> (μΑ	ent		erature icient vV/K)	•	Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current I <sub>ZSM</sub> (A) <sup>[2]</sup> Max  1.0  1.0  0.9  0.8  0.7  0.6  0.5	
		I <sub>Z</sub> = 2 i	mA	$I_Z = 0$	.5 mA	$I_Z = 2 \text{ mA}$				I <sub>Z</sub> = 2	mA			I <sub>ZSM</sub> (A)[2]	
		Min	Max	Тур	Max	Тур	Max	Max	V <sub>R</sub> (V)	Min	Тур	Max	Max	Max	
27	Α	26.73	27.27	65	300	25	80	0.05	18.9	21.4	23.4	25.3	50	1.0	
	В	26.5	27.5												
	С	25.1	28.9												
30	Α	29.7	30.30	70	300	30	80	0.05	21	24.4	26.6	29.4	50	1.0	
	В	29.4	30.6												
	С	28.0	32.0												
33	Α	32.67	33.33	75	325	35	80	0.05	23.1	27.4	4 29.7	33.4	45	0.9	
	В	32.3	33.7												
	С	31.0	35.0												
36	Α	35.64	36.36	80	350	35	90	0.05	25.2	30.4	33.0	37.4	45	0.8	
	В	35.3	36.7												
	С	34.0	38.0												
39	Α	38.61	39.39	80	350	40	130	0.05	27.3	27.3 33.4	36.4	4 41.2	45	0.7	
	В	38.2	39.8												
	С	37.0	41.0												
43	Α	42.57	43.43	85	375	45	150	0.05	30.1	37.6	41.2	46.6	40	0.6	
	В	42.1	43.9												
	С	40.0	46.0												
47	В	46.1	47.9	85	375	50	170	0.05	32.9	42.0	46.1	51.8	40	0.5	
	С	44.0	50.0	†											
51	Α	50.49	51.51	90	400	60	180	0.05	35.7	46.6	51.0	57.2	40	0.4	
	В	50.0	52.0	†					0 00.7	10.0					
	С	48.0	54.0												

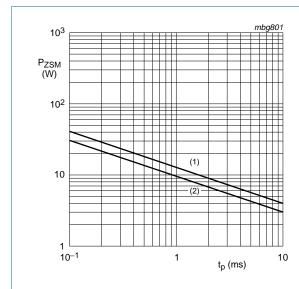
<sup>[2]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \, ^{\circ}C$  before surge

 Table 9.
 Characteristics per type;
 BZX84-A27 to BZX84-C75 ...continued

BZX84- xxx	Sel	Working voltage V <sub>Z</sub> (V) I <sub>Z</sub> = 2 mA		Differential resistance $r_{dif} (\Omega)$			Reverse current I <sub>R</sub> (μA)		Temperature coefficient S <sub>Z</sub> (mV/K)			Diode capacitance C <sub>d</sub> (pF)[1]	Non-repetitive peak reverse current	
				$I_Z = 0.5 \text{ mA}$		I <sub>Z</sub> = 2 mA				I <sub>Z</sub> = 2 mA			I <sub>ZSM</sub> (A)[2]	
		Min	Max	Тур	Max	Тур	Max	Max	V <sub>R</sub> (V)	Min	Тур	Max	Max	Мах
56	В	54.9	57.1	100	425	70	200	0.05	39.2	52.2	57.0	63.8	40	0.3
	С	52.0	60.0											
62	В	60.8	63.2	120	450	80	215	0.05	43.4	58.8	64.4	71.6	35	0.3
	С	58.0	66.0											
68	В	66.6	69.4	150	475	90	240	0.05	47.6	65.6	71.7	79.8	35	0.25
	С	64.0	72.0											
75	Α	74.25	75.75	170	500	95 2	255	0.05	52.5	73.4	80.2	88.6	35	0.20
	В	73.5	76.5											
	С	70.0	79.0											

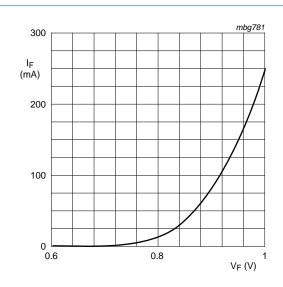
<sup>[1]</sup>  $f = 1 \text{ MHz}; V_R = 0 \text{ V}$ 

<sup>[2]</sup>  $t_p = 100 \mu s$ ; square wave;  $T_j = 25 \, ^{\circ} C$  before surge



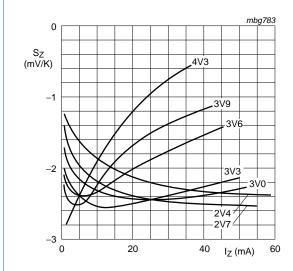
- (1)  $T_i = 25$  °C (before surge)
- (2)  $T_i = 150 \,^{\circ}\text{C}$  (before surge)

Fig 1. Non-repetitive peak reverse power dissipation as a function of pulse duration; maximum values



T<sub>j</sub> = 25 °C

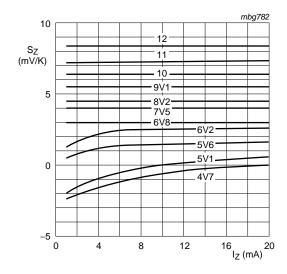
Fig 2. Forward current as a function of forward voltage; typical values



BZX84-A/B/C2V4 to BZX84-A/B/C4V3

 $T_j = 25 \,^{\circ}\text{C}$  to 150  $^{\circ}\text{C}$ 

Fig 3. Temperature coefficient as a function of working current; typical values



BZX84-A/B/C4V7 to BZX84-A/B/C12

 $T_j = 25 \,^{\circ}\text{C}$  to 150  $^{\circ}\text{C}$ 

Fig 4. Temperature coefficient as a function of working current; typical values

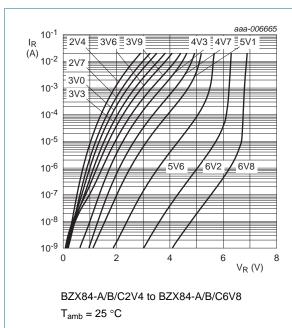
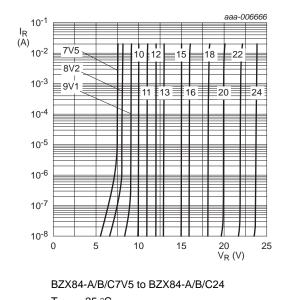
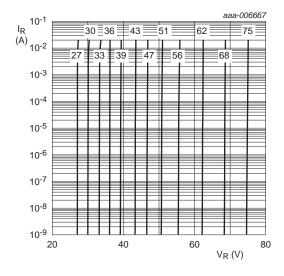


Fig 5. Reverse current as a function of reverse voltage; typical values



T<sub>amb</sub> = 25 °C

Fig 6. Reverse current as a function of reverse voltage; typical values



BZX84-A/B/C27 to BZX84-A/B/C75

 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 7. Reverse current as a function of reverse voltage; typical values

## 8. Test information

## 8.1 Quality information

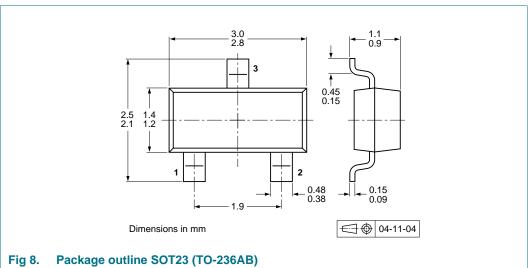
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

BZX84\_SER

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## Package outline



## 10. Packing information

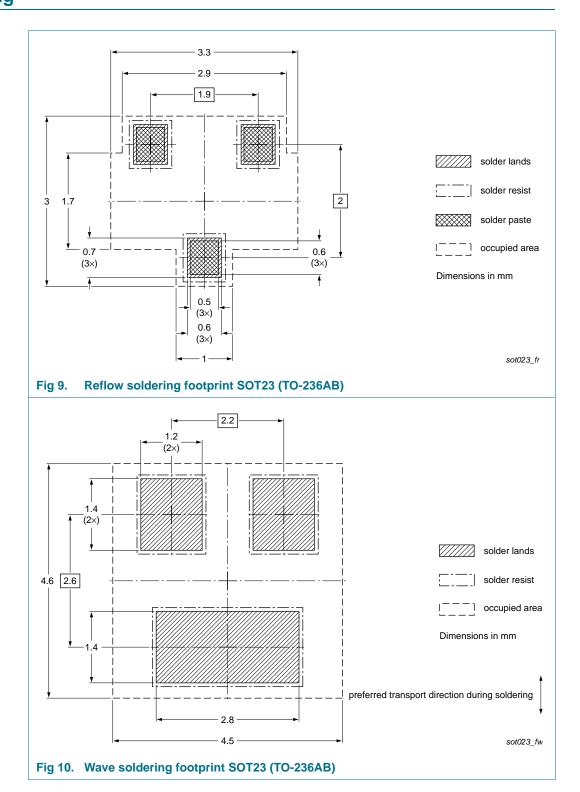
Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BZX84 series <sup>[2]</sup>	SOT23 (TO-236AB)	4 mm pitch, 8 mm tape and reel	-215	-235

- [1] For further information and the availability of packing methods, see Section 14.
- [2] The series includes 37 breakdown voltages with nominal working voltages from 2.4 V to 75 V and  $\pm 1\,\%$ , ±2 % and ±5 % tolerances.

## 11. Soldering



# 12. Revision history

## Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BZX84_SER v.6	20140306	Product data sheet	-	BZX84_SER v.5
Modifications:	Descriptive ti	tle of the document correcte	ed	
BZX84_SER v.5	20130918	Product data sheet	-	BZX84_SER v.4
BZX84_SER v.4	20130322	Product data sheet	-	BZX84_SERIES v.3
BZX84_SERIES v.3	20030410	Product data sheet	-	BZX84 v.2
BZX84 v.2	19990518	Product specification	-	BZX84 v.1
BZX84 v.1	19960426	Product specification	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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**BZX84** series

#### Voltage regulator diodes

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